

MMBA812M6 PNP EPITAXIAL SILICON TRANSISTOR

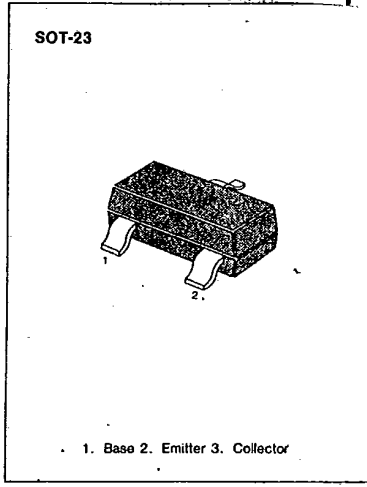
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GENERAL PURPOSE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	40	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5086 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} =40V, I _E =0		100	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0		100	nA
DC Current Gain	h _{FE}	V _{CE} =6V, I _C =1mA	200	400	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C =30mA, I _B =3mA		0.5	V
Base-Emitter On Voltage	V _{BE (on)}	I _C =1mA, V _{CE} =6V		0.8	V

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Marking

